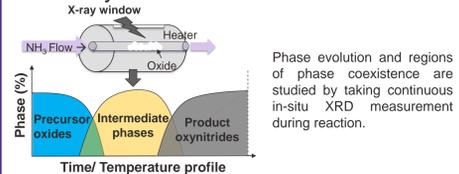


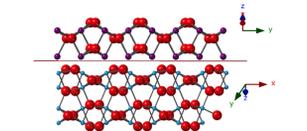
Synthesis of oxynitrides for photocatalysis

Transition-metal oxynitrides, materials with both O and N anions, are emerging photo- and electro- catalytic materials due to their unique physical, chemical and opto-electronic properties. Oxynitrides are synthesized by flowing NH_3 over an oxide precursor at elevated temperatures. Final products are sensitive to heating profile, precursor, and extent of reaction, making it challenging to obtain single phase products reproducibly, which is key for performing further characterization studies. Probing reaction pathway via in-situ studies corroborated with DFT calculations, allows more controlled synthesis of these oxynitrides.

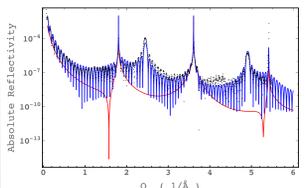
In situ Synthesis of TaON and Mo-O-N



Thin Film Growth of Ta-O-N

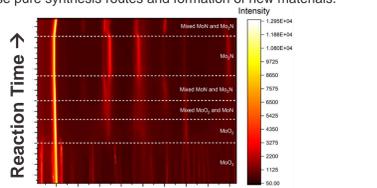


Single crystal, epitaxial Ta-O-N films are grown by PLD. By matching the TaON lattice constants to the substrate, specific phases of oxynitride can be targeted.



A high quality epitaxial film of TaO₂ (101)/Al₂O₃ (012) provides starting point of oxynitride film growth.

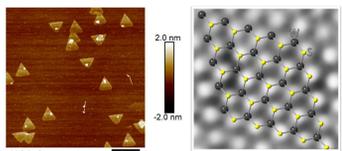
Allows direct observation and identification of intermediate phases, thereby guiding phase pure synthesis routes and formation of new materials.



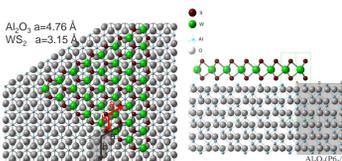
Currently: Elise Goldfine (PhD student) [Collaboration with Prof. Sossina Haile]

Characterization of 2D transition metal dichalcogenides

Growing 2D materials epitaxially on single crystal substrates provides a means for controlling their orientation.

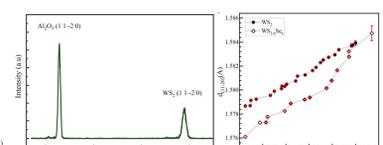


AFM image showing the atomic resolved surface of the WS₂ layer. The overlay shows the atom locations.



WS₂ has a van der Waals epitaxial relation with the substrate c-Al₂O₃. The orientation relation is WS₂(0001)//Al₂O₃(0001) and WS₂(110)//Al₂O₃(110).
Currently: Achari Kondapalli (Postdoc)

- WSe₂ is of interest as a 2D semiconductor (SC) with a direct band-gap. Due to low doping levels, it is an intrinsic SC and shows ambipolar transport. This affords the possibility to realize devices with the Fermi level located in the valence band, where the spin/valley coupling is strong and leads to novel and interesting physics.
- WS₂ and WSe₂ were deposited on sapphire substrates using HT-MOCVD by collaborators at The 2D Crystal Consortium, Penn State University.
- Atomic resolution AFM was carried out with our newly installed VT-AFM.
- Synchrotron X-ray characterization (CTR and XSW) of the structures is ongoing.



In-plane XRD confirming the orientation relation WS₂(110)//Al₂O₃(110). High temperature in-plane XRD elucidating the Se doping effect on the thermal expansion behavior of the WS₂.



From Left: Guenna, Achari, Prof. Bedzyk, Anusheela, Kathy, Roger, Elise, Bruce, Joey, Rachel, Carlos, Sumit, Yanna, Anthony, Jerry

Wide Angle X-ray Scattering (WAXS)

Small Angle X-ray Scattering (SAXS)

X-Ray Absorption Fine Structure (XAFS)

X-Ray Standing Wave (XSW)

X-Ray Reflectivity (XRR)

INTERFACIAL SCIENCE
by its very nature brings together a diverse interests in oxide films, catalysis, semiconductors, nano-science, bio-membranes, surface physics, corrosion, and electrochemistry.

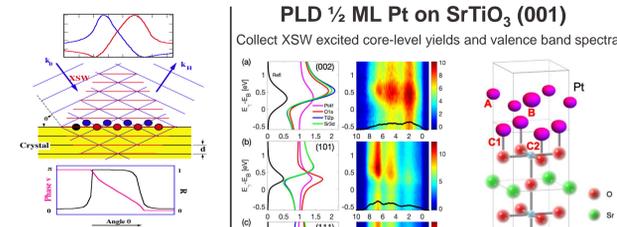
One of many grand challenges in the overall interdisciplinary field of interfacial science is the need to observe and control the assembly of atoms, molecules and supported nanoparticles at well-defined interfaces in complex environments.

With atomic resolution and high penetrating power, we are developing and applying sophisticated *in situ* X-ray methods to meet these challenges.

Atomic-scale x-ray interface studies of heterogeneous catalytic systems

PLD 1/2 ML Pt on SrTiO₃ (001)

Collect XSW excited core-level yields and valence band spectra



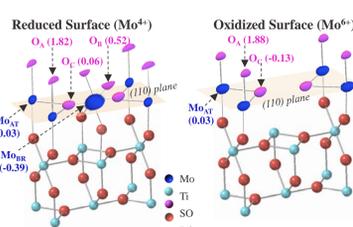
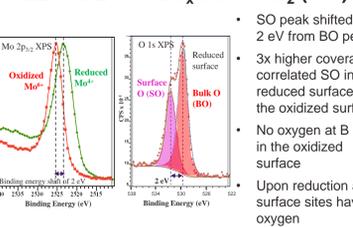
X-ray standing wave → Interference between incident and Bragg reflected X-ray planes waves, XSW period = d

Scanning in q thru Bragg peak → XSW phase shift by $\frac{1}{2}$ → modulation in XRF (element specific) or XPS (chemical state specific) yield

Fourier summation of multiple planes → 3D, model-independent, real-space map of emitter atoms with sub-Å

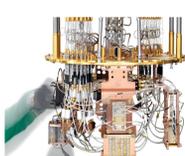
A novel method to determine site-specific valence electrons contribution to density of states

ALD 1 ML of MoO_x on α -TiO₂ (110)



- SO peak shifted to by 2 eV from BO peak
- 3x higher coverage of correlated SO in the reduced surface than the oxidized surface
- No oxygen at B site in the oxidized surface
- Upon reduction all 3 surface sites have oxygen
- Mo 2p_{3/2} peak shifted by 2 eV lower by reduction
- No bridging Mo in the oxidized surface
- Upon reduction, most Mo from AT site → BR site

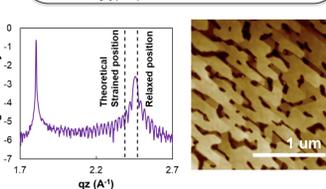
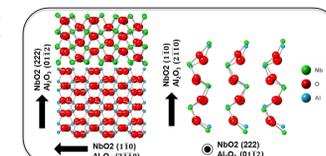
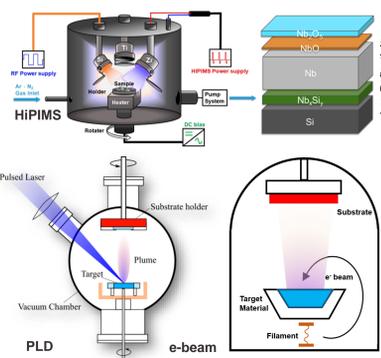
Improving the coherence time of superconducting qubits through materials characterization and optimization



- Superconducting qubits use Josephson junction (JJ) circuit elements to create controllable and readable qubits.
- Qubit architecture of 2D and 3D transmon designed limit noise.
- Materials defects, loss, and participation are sources of substantial decoherence in qubits.
- Fabrication of JJs, resonators, and transmons are used to measure qubit quality of synthesized material and compare thin film structures for future chip fabrication.
- Northwestern University has partnered with Fermilab and Rigetti Computing to fundamentally understand the source of decoherence and implement mitigation strategies.

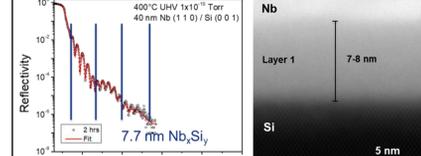
Niobium thin films are grown via Pulsed Laser Deposition (PLD), Magnetron Sputtering, High-power Impulse Magnetron Sputtering (HIPIMS), and electron beam evaporation (e-beam) on silicon and sapphire substrates.

These techniques are used to compare growth techniques for use in industry as well as to compare the effect of film microstructure on qubit performance.



Depending on the substrate and growth technique, the films may be epitaxial, textured, polycrystalline, or amorphous.

X-ray diffraction is used to determine the crystal structure, crystallinity, and lattice mismatch. Control of the structure is studied for the use in superconducting qubits.



Formation of unwanted phases in the film interfaces and bulk such as niobium hydrides and silicides are studied with numerous techniques including X-ray Reflectivity, Cross-section TEM, Atomic Force Microscopy, and X-ray Diffraction, and X-ray Photoelectron Spectroscopy. Interdiffusion of silicon at the substrate interface causes the formation of amorphous Nb₃Si₃. Hydrogen can be incorporated into the bulk via chemical and cryogenic experiment, creating Nb₃H₃.

Currently: Carlos Torres (PhD student), David Garcia Wetten (PhD student), K.V.L.V Narayanachari (Postdoc)